

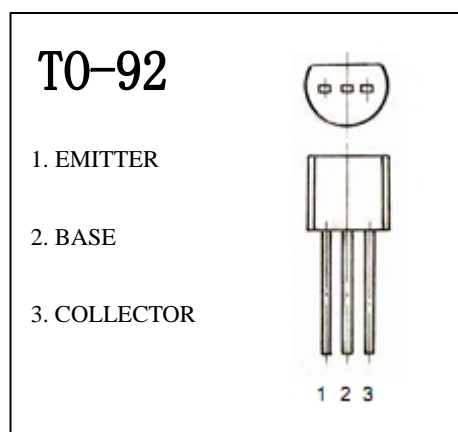
# 深圳市晶泰源电子有限公司

2SC1008

TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	80	V
VCEO	Collector-Emitter Voltage	60	V
VEBO	Emitter-Base Voltage	8	V
IC	Collector Current	0.7	A
PC	Collector Power Dissipation	800	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	80			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	60			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	8			V
Collector cut-off current	ICBO	VCB=60V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=5V, IC=0			0.1	μA
DC current gain	HFE	Vce=2V, Ic=50mA	40		400	
Collector-emitter saturation voltage	VCE(sat)	IC=500mA, IB=50mA			0.4	V
Base-emitter saturation voltage	VBE(sat)	IC=500mA, IB=50mA			1.1	V
Transition Frequency	fT	VCE=10V, IC=50mA	30	50		MHZ
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		8		pF